



# PJS6461-AU

## 60V P-Channel Enhancement Mode MOSFET

Voltage

-60 V

Current

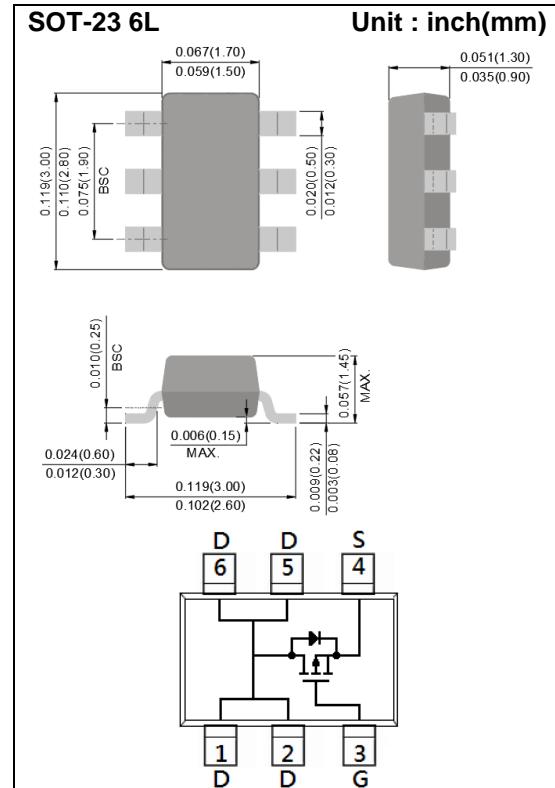
-3.2A

### Features

- $R_{DS(ON)}$ ,  $V_{GS} @ -10V$ ,  $I_D @ -3.2A < 110m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS} @ -4.5V$ ,  $I_D @ -1.6A < 130m\Omega$
- High switching speed
- Improved dv/dt capability
- Low gate charge
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 Standard

### Mechanical Data

- Case : SOT-23 6L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0005 ounces, 0.014 grams



### Maximum Ratings and Thermal Characteristics ( $T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	$V_{DS}$	-60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current <sup>(Note 4)</sup>	$I_D$ $T_A=25^\circ C$	-3.2	A
	$I_D$ $T_A=70^\circ C$	-2.5	
Pulsed Drain Current <sup>(Note 1)</sup>	$I_{DM}$	-20	
Power Dissipation	$P_D$ $T_A=25^\circ C$	2	W
	$P_D$ $T_A=70^\circ C$	1.3	
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~150	°C
Typical Thermal Resistance - Junction to Ambient <sup>(Note 4,5)</sup>	$R_{\theta JA}$	62.5	°C/W



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## Electrical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
<b>Static</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_{\text{D}}=-250\mu\text{A}$	-60	-	-	V
Gate Threshold Voltage	$\text{V}_{\text{GS}(\text{th})}$	$\text{V}_{\text{DS}}=\text{V}_{\text{GS}}, \text{I}_{\text{D}}=-250\mu\text{A}$	-1.0	-1.6	-2.5	
Drain-Source On-State Resistance	$\text{R}_{\text{DS}(\text{on})}$	$\text{V}_{\text{GS}}=-10\text{V}, \text{I}_{\text{D}}=-3.2\text{A}$	-	88	110	$\text{m}\Omega$
		$\text{V}_{\text{GS}}=-4.5\text{V}, \text{I}_{\text{D}}=-1.6\text{A}$	-	110	130	
Zero Gate Voltage Drain Current	$\text{I}_{\text{DSS}}$	$\text{V}_{\text{DS}}=-60\text{V}, \text{V}_{\text{GS}}=0\text{V}$	-	-	-1	$\mu\text{A}$
Gate-Source Leakage Current	$\text{I}_{\text{GSS}}$	$\text{V}_{\text{GS}}=\pm 20\text{V}, \text{V}_{\text{DS}}=0\text{V}$	-	-	$\pm 100$	$\text{nA}$
<b>Dynamic</b> <sup>(Note 6)</sup>						
Total Gate Charge	$\text{Q}_g$	$\text{V}_{\text{DS}}=-30\text{V}, \text{I}_{\text{D}}=-3.2\text{A}, \text{V}_{\text{GS}}=-10\text{V}$ <sup>(Note 2,3)</sup>	-	10	-	$\text{nC}$
Gate-Source Charge	$\text{Q}_{\text{gs}}$		-	1.6	-	
Gate-Drain Charge	$\text{Q}_{\text{gd}}$		-	3	-	
Input Capacitance	$\text{C}_{\text{iss}}$	$\text{V}_{\text{DS}}=-30\text{V}, \text{V}_{\text{GS}}=0\text{V}, \text{f}=1\text{MHZ}$	-	785	-	$\text{pF}$
Output Capacitance	$\text{C}_{\text{oss}}$		-	176	-	
Reverse Transfer Capacitance	$\text{Crss}$		-	116	-	
Turn-On Delay Time	$\text{td}_{(\text{on})}$	$\text{V}_{\text{DS}}=-30\text{V}, \text{I}_{\text{D}}=-1\text{A}, \text{V}_{\text{GS}}=-10\text{V}, \text{R}_g=6.2\Omega$ <sup>(Note 2,3)</sup>	-	8	-	$\text{ns}$
Turn-On Rise Time	$\text{tr}$		-	15	-	
Turn-Off Delay Time	$\text{td}_{(\text{off})}$		-	43	-	
Turn-Off Fall Time	$\text{tf}$		-	8.4	-	
<b>Drain-Source Diode</b>						
Maximum Continuous Drain-Source Diode Forward Current	$\text{I}_{\text{s}}$	---	-	-	-2	A
Diode Forward Voltage	$\text{V}_{\text{SD}}$	$\text{I}_{\text{s}}=-1\text{A}, \text{V}_{\text{GS}}=0\text{V}$	-	-0.77	-1	V

### NOTES :

1. Pulse width $\leq 300\text{us}$ , Duty cycle $\leq 2\%$ .
2. Essentially independent of operating temperature typical characteristics.
3. Repetitive rating, pulse width limited by junction temperature  $\text{T}_{\text{J}(\text{MAX})}=150^\circ\text{C}$ . Ratings are based on low frequency and duty cycles to keep initial  $\text{T}_{\text{J}}=25^\circ\text{C}$ .
4. The maximum current rating is package limited.
5.  $\text{R}_{\thetaJA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
6. Guaranteed by design, not subject to production testing.



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## TYPICAL CHARACTERISTIC CURVES

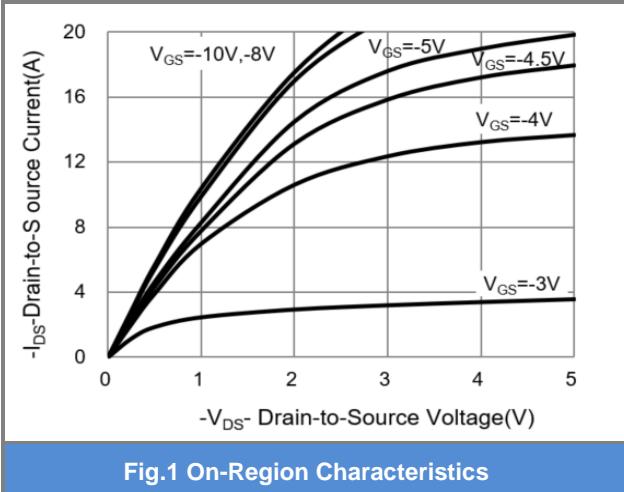


Fig.1 On-Region Characteristics

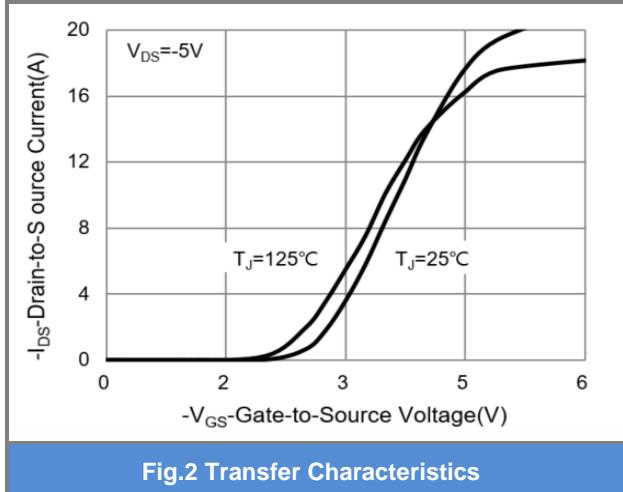


Fig.2 Transfer Characteristics

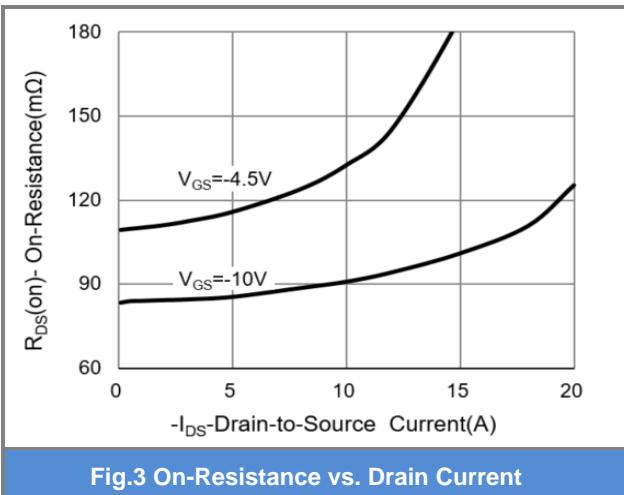


Fig.3 On-Resistance vs. Drain Current

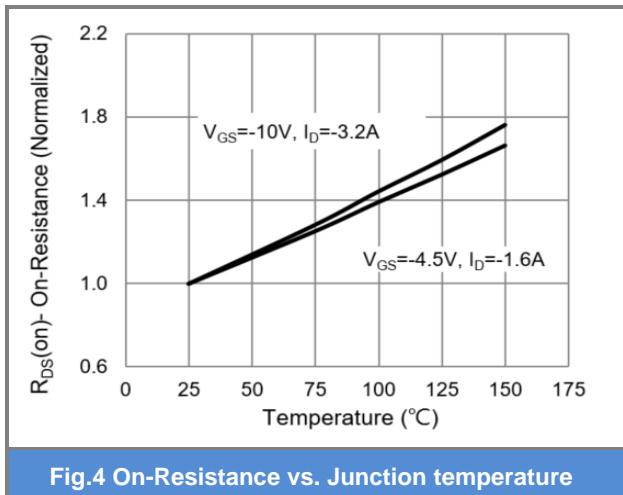


Fig.4 On-Resistance vs. Junction temperature

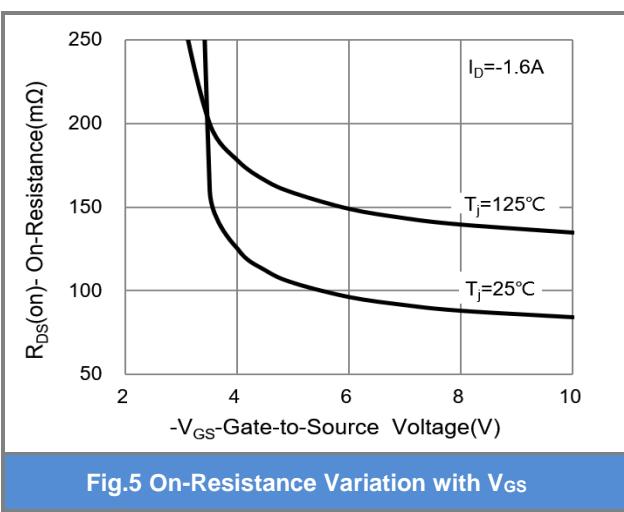


Fig.5 On-Resistance Variation with V<sub>GS</sub>

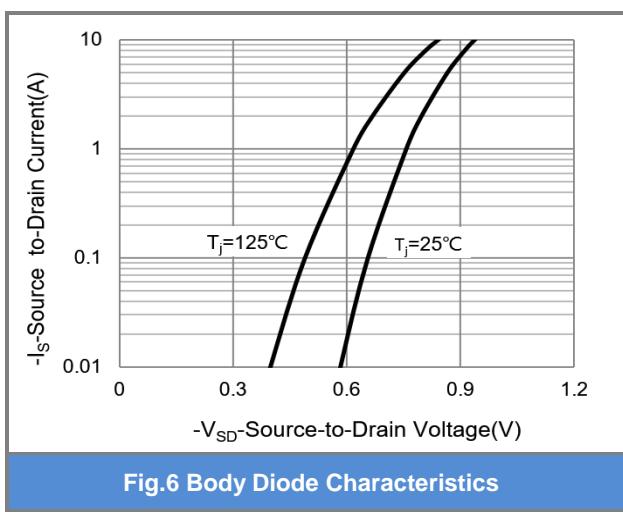


Fig.6 Body Diode Characteristics



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## TYPICAL CHARACTERISTIC CURVES

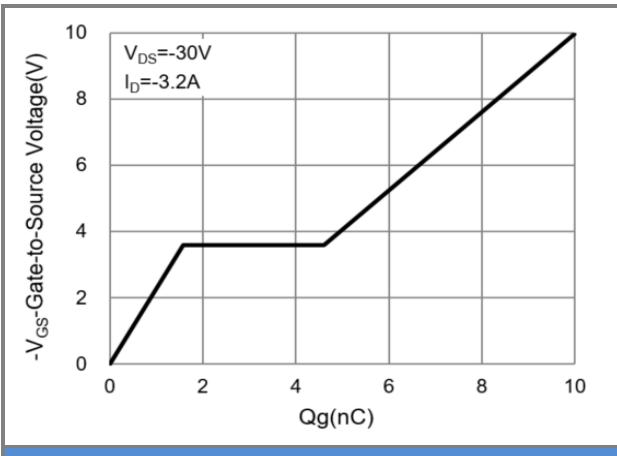


Fig.7 Gate-Charge Characteristics

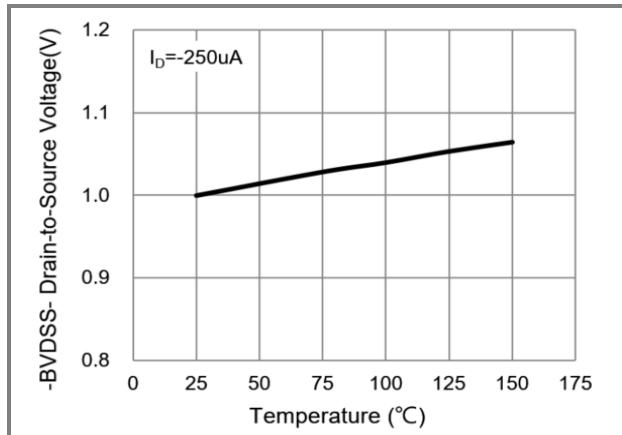


Fig.8 Breakdown Voltage Variation vs. Temperature

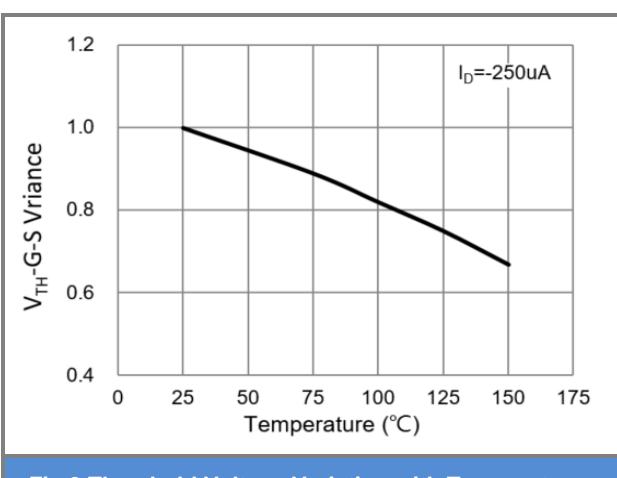


Fig.9 Threshold Voltage Variation with Temperature

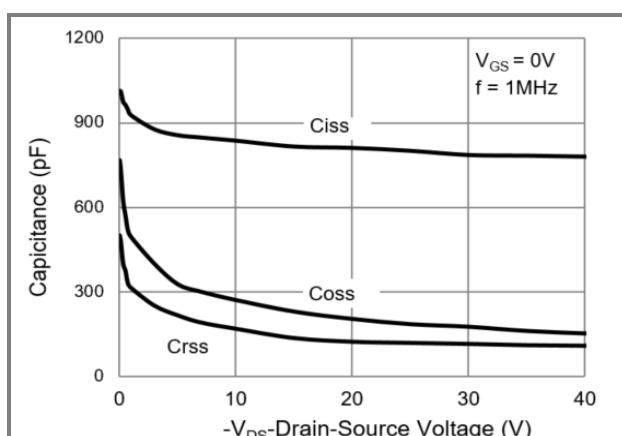


Fig.10 Capacitance vs. Drain-Source Voltage

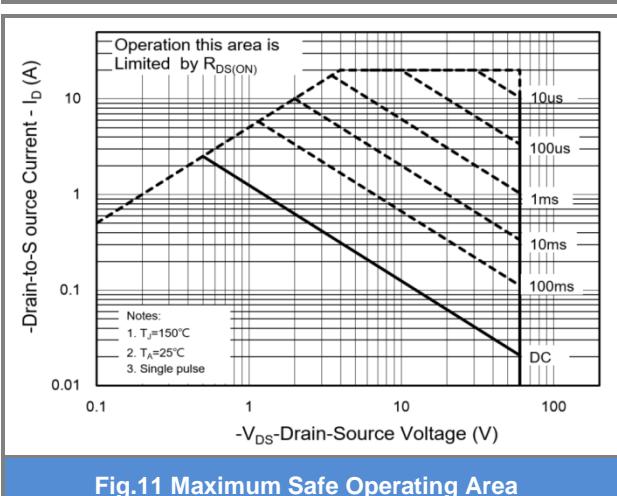


Fig.11 Maximum Safe Operating Area

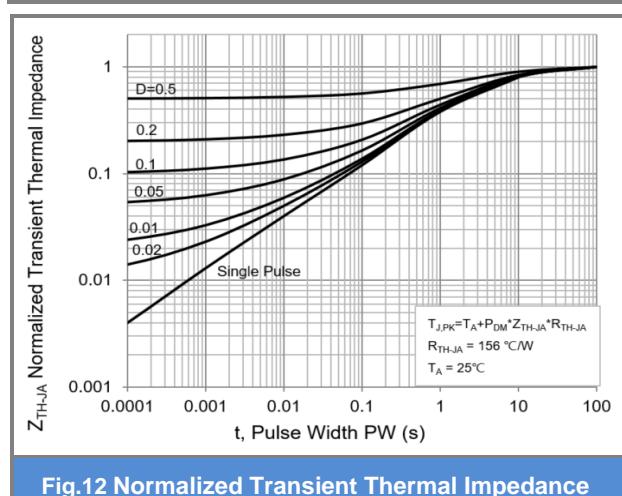


Fig.12 Normalized Transient Thermal Impedance



# PJS6461-AU

## Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJS6461-AU_S1_000A1	SOT-23 6L	3K pcs / 7" reel	S61	Halogen free RoHS compliant

## Mounting Pad Layout

